



#14
Arnold B.
D. Small Logan
D-500.40010X00
1-22-03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: K. OHNISHI, et al.

APPLICATION NO.: 09/829,969

FILED: April 11, 2001

FOR: SEMICONDUCTOR DEVICE AND PROCESS FOR
PRODUCING THE SAME

ART UNIT: 2818

EXAMINER: Tran

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TECHNOLOGY CENTER 2800
DEC 27 2002

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

December 26, 2002

Sir:

In response to the further Office Action dated September 26, 2002, the

01/29/2003 following amendments and remarks are respectfully submitted in connection with the
01 FC:1201 84.00 CH
02 FC:1202 above identified application.

IN THE CLAIMS:

Please insert additional Claims 33 - 40, as follows:

Sub C8
33. A semiconductor device comprising, on a substrate, at least one MOS transistor, wherein a gate electrode of the MOS transistor is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a reaction barrier layer and a metallic layer, formed in that order beginning with the silicon layer.